

(11)

EP 1 158 568 A2

(12)

EUROPEAN PATENT APPLICATION

(43) Date of publication:
28.11.2001 Bulletin 2001/48

(51) Int Cl.7: H01L 21/00, C23C 16/458,
H01J 9/00

(21) Application number: 01111452.7

(22) Date of filing: 10.05.2001

(84) Designated Contracting States:
AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU
MC NL PT SE TR
Designated Extension States:
AL LT LV MK RO SI

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(30) Priority: 24.05.2000 US 577104

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(54) Plasma assisted semiconductor substrate processing chamber

(57) A plasma assisted semiconductor substrate processing chamber having a plurality of electrically conductive bridges for preventing electrical arcing in the

chamber. More particularly, the chamber has a plurality of electrically conductive bridges that connect a portion of a substrate support member with a portion of the chamber walls.

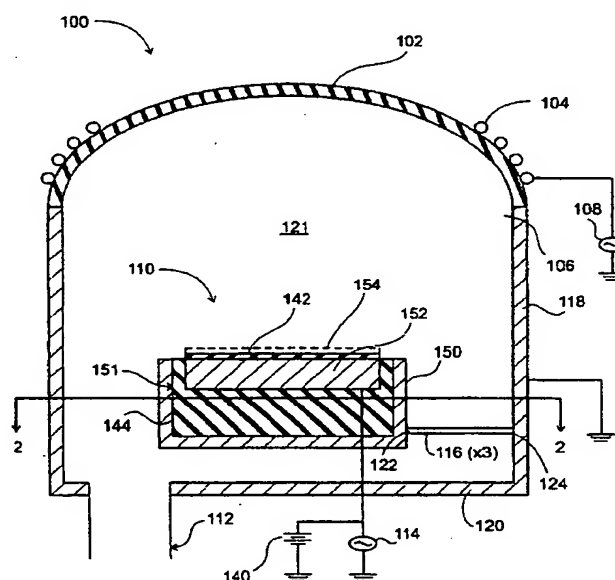


Fig. 1

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Description

[0001] The present invention relates to a plasma assisted semiconductor substrate processing chamber. More particularly, the invention relates to a plasma assisted semiconductor substrate processing chamber having a plurality of electrically conductive bridges that connect a portion of a substrate support member with a portion of the chamber walls.

[0002] In plasma assisted semiconductor substrate processing chambers, an electrical discharge, or electrical arcing phenomenon can occur, particularly when a high frequency radio frequency (RF) power source is employed to power a substrate electrode in a substrate support member and when the chamber is large (e.g., capable of processing 300 mm substrates). The electrical arc can cause sputtering of chamber wall material that deposits on and contaminates a substrate that is presently in the chamber or a substrate that is later introduced into the chamber.

[0003] For example, arcing has been observed in a plasma assisted chemical vapor deposition (CVD) chamber that is designed to process 300 mm substrates. The chamber has electrically conductive walls that are DC grounded. One RF power source is utilized for plasma generation while another RF power source powers a substrate electrode in a substrate support member to provide substrate biasing during processing. A single electrically conductive bridge connects a grounded portion of the substrate support member with a portion of the grounded chamber walls, providing an RF ground path from the substrate support member to the chamber walls. Within such a chamber, arcing from the plasma to the chamber sidewalls has been observed when the RF power source coupled to the substrate electrode is activated.

[0004] Arcing from the plasma to the chamber walls has been determined to be the result of chamber geometry being such that the largest electrical RF return path length exceeds approximately 1/4 wavelength of a surface RF wave inside the chamber. According to RF theory, high density, magnetic field-free plasma sources, as may be used in certain CVD chambers, produce plasmas that are opaque to RF fields within a frequency range from 0 - 200 MHz. For this reason, RF currents flow along the surface of the plasma. In effect, the surface of the plasma forms one electrode and the chamber wall forms another electrode of a waveguide. The width of the waveguide is the width of the plasma sheath and the length of the waveguide is the inner circumference of the chamber. When the largest electrical RF return path length exceeds approximately 1/4 of a surface RF wavelength inside the chamber, a standing wave will form "RF nodes". The RF nodes arise at random locations along the surface of the chamber walls. Extremely high voltage can be created between the RF nodes and a plasma within the chamber, causing an electrical discharge between the plasma and the chamber walls,

which is known as electrical arcing or unipolar arcing.

[0005] According to surface wave theory, in the presence of a plasma, an RF wave propagated along conductive chamber surfaces takes the form of a surface wave, with its wavelength and phase velocity reduced by a factor of approximately five as compared with free space [Eqs (1,2)]. As stated above, electrical arcing will occur when the largest electrical RF return path exceeds approximately 1/4 of a surface RF wavelength inside the chamber. Since the surface RF wavelength in a chamber is approximately 1/5 of the free space wavelength, electrical arcing occurs when the inner circumference of the chamber exceeds approximately (1/4)·(1/5) or 1/20 of a free space RF wavelength.

[0006] The following surface wave theory equation shows that, as discussed above, the RF wavelength and phase velocity along chamber surfaces (i.e., in the waveguide formed between the plasma and the chamber walls) are reduced by a factor of approximately five compared to free space, in the limit of $\omega_{pe}/\omega \gg 1$, and $\delta \gg d$,

$$V_{\text{phase}} = c/(\delta/d+1)^{1/2} \quad (1)$$

where:

V_{phase} is the RF phase velocity along a conducting surface;

c is the speed of light;

$\delta = c/\omega_{pe}$ is the RF skin depth, where ω_{pe} is the plasma frequency;

$d \equiv V_{te}/\omega_{pe} f(V_{rf}, T_e)$ is the plasma sheath thickness, V_{te} is the electron thermal velocity, and $f(T_e, V_{rf})$ depends on the sheath model and is a function of the electron temperature T_e and the RF voltage V_{rf} .

For $T_e = 5$ eV and $f(V_{rf}, T_e) = 10$ (d is 10 times the Debye length),

$$V_{\text{phase}} = c/(\delta/d+1)^{1/2} \approx c/5$$

The Equation (1) and (2) can also be written as:

$$\lambda_{\text{surface}} \equiv \lambda_0/(\delta/d+1)^{1/2} \approx \lambda_0/5$$

where λ_{surface} is the RF wavelength along the chamber walls, and λ_0 is the free space wavelength of the RF signal.

Therefore, where the largest electrical RF return path exceeds approximately 1/4 of the surface RF wavelength, or 1/20 of a free space RF wavelength inside the chamber, electrical arcing can occur and can cause sputtering of chamber wall material. In chambers with a single conductive bridge leading from a portion of a substrate support member to DC grounded, conductive

chamber walls, the largest electrical RF return path is at least about equal to the inner circumference of the chamber wall. Therefore, in such a single bridge chamber, electrical arcing can occur where the inner chamber wall circumference exceeds approximately 1/4 of a surface RF wavelength. Furthermore, in a single bridge chamber, electrical arcing can occur if the inner chamber wall circumference exceeds approximately 1/20 of a free space RF wavelength.

[0007] Electrical arcing has particularly become a problem as larger plasma assisted chambers are being designed and used to accommodate 300 mm diameter substrates. Chambers that accommodate large substrates generally have commensurately larger inner chamber wall circumferences. Therefore, for a given RF power frequency utilized, when the chamber is designed large enough so that the chamber wall inner circumference exceeds approximately 1/4 of a surface RF wavelength or approximately 1/20 of a free space RF wavelength for the highest frequency RF power employed to power a substrate electrode in a substrate support member, electrical arcing can occur in the chamber.

[0008] In addition, in some instances a second or greater harmonic frequency of a surface wave inside the chamber has sufficient energy to lead to RF nodes and cause electrical arcing. Since each numerically greater harmonic has a wavelength half as great as the previous harmonic, the chamber wall inner circumference that might give rise to electrical arcing for each succeeding harmonic is half that of the previous harmonic.

[0009] Therefore, a need exists in the art for a plasma assisted semiconductor substrate processing chamber in which electrical arcing caused by surface wave effects is eliminated.

[0010] The present invention provides a plasma assisted semiconductor substrate processing chamber having a plurality of electrically conductive bridges connecting a portion of a substrate support member with a portion of the chamber walls. The plurality of bridges can prevent electrical arcing from occurring in the chamber, particularly when a high frequency, radio frequency (RF) power source is employed to power a substrate electrode in a substrate support member within a large chamber. In one aspect, the invention provides a plasma assisted chamber having a plurality of electrically conductive bridges connecting a portion of a substrate support member with a portion of the DC grounded chamber walls.

[0011] The teachings of the present invention can be readily understood by considering the following detailed description of embodiments of the invention in conjunction with the accompanying drawings, in which:

FIG. 1 shows a cross sectional side view of a chamber having a plurality of bridges;
FIG. 2 shows a cross sectional perspective view of the chamber taken along line 2-2 of FIG. 1; and
FIG. 3 shows a cross sectional perspective view of

a chamber containing a second embodiment of the invention.

[0012] The present invention generally provides a plasma assisted semiconductor substrate processing chamber having a plurality of electrically conductive bridges. In one embodiment, the invention provides a chamber having a plurality of electrically conductive bridges connecting a portion of a substrate support member with the DC grounded chamber walls for preventing electrical arcing in the chamber.

[0013] After considering the following description, those skilled in the art will clearly realize that the teachings of the invention can be readily utilized to prevent electrical arcing in plasma assisted semiconductor substrate processing chambers, particularly when a high frequency RF power source is employed to power a substrate electrode in a substrate support member within a relatively large chamber.

[0014] FIG. 1 shows a cross sectional side view of a plasma assisted chemical vapor deposition (CVD) chamber 100 having a plurality of bridges 116 (one is shown). Plasma assisted CVD chambers are well known in the art. The chamber 100 generally includes a processing region 121 enclosed by a bottom 120, a sidewall 118, and a dome 102. A gas inlet 106 is formed in the sidewall 118, and a gas outlet 112 is formed in the bottom 120. A coiled antenna 104 is mounted on the dome 102 and coupled to a first RF power source 108.

The coiled antenna 104, when driven by RF power source 108, couples energy to a gas or gases in the chamber 100 to form a plasma in the chamber 100. The sidewall 118 and bottom 120 are DC and RF grounded.

[0015] A substrate support member 110 is disposed in the processing region 121. The substrate support member 110 may comprise a grounded electrically conductive bucket 150 and an electrostatic chuck 151 disposed within the bucket 150. The electrostatic chuck 151 may comprise an insulating material 144 and an electrically conductive substrate electrode 152 disposed in a recess formed in the insulating material 144. A thin layer of dielectric material 142 is disposed on top of the substrate electrode 152. A second RF power source 114 and a chucking power source 140 are coupled to the substrate electrode 152. The second RF power source 114 provides substrate biasing during substrate processing, and the chucking power source 140 provides DC power and is used to secure or chuck a substrate 154 to the dielectric material 142 during substrate processing. A plurality (preferably three) bridges 116 that are electrically conductive are connected at a first end 122 to the bucket 150 and at a second end 124 end to a portion of the chamber sidewall 118.

[0016] FIG. 2 shows a cross sectional perspective view of the plasma assisted chamber 100 taken along line 2-2 of FIG. 1. The three bridges 116 are equally spaced from one another. Each bridge 116 is connected at its first end 122 to a portion of the outer surface 201

of the sidewall 202 of the bucket 150 and at its second end 124 to a portion of the inner surface 204 of the DC and RF grounded chamber sidewall 118. Each of the bridges 116 thereby forms an electrical ground path between the bucket 150 of the substrate support member 110 and the grounded chamber sidewall 118. The bridges 116 are conductive, and may be fabricated of materials such as aluminum. The bridges 116 have physical dimensions that form a surface area that is sufficient to carry the expected RF currents from the substrate support member 110 to the chamber walls. In the embodiment shown, the bridges 116 are 4 inches wide and 2 inches thick. Various embodiments of the bridges are possible, including solid, as shown, or mesh (as described below with reference to FIG. 3).

[0017] In operation, the bridges 116 prevent electrical arcing that could otherwise occur when the second RF power source 114 is activated. An electrical arc is an electrical discharge that can occur between plasma in the chamber 100 and a point along the inner surface 204 of the chamber sidewall 118 where an RF node has formed. Since chamber 100 has three bridges 116, the largest electrical RF return path is approximately 1/3 of a circumference of the inner surface 204 of the chamber sidewall 118, i.e., the bridges 116 provide ground points along the waveguide formed by the plasma and chamber walls. Thus, for a given second RF power source 114 frequency, the plurality of bridges 116 reduces the largest electrical RF return path to substantially less than 1/4 of a surface RF wavelength, or substantially less than 1/20 of a free space RF wavelength, and thereby increases the inner chamber wall circumference that can be utilized without causing electrical arcing in the chamber. Consequently, by utilizing a plurality of bridges instead of only one bridge, chamber size can be increased and electrical arcing avoided. Further increases in chamber size can be accommodated by adding more bridges. If arcing due to energy in harmonic frequencies is expected, additional bridges may be used to reduce the distance between bridges to substantially less than 1/4 of the surface wavelength of the harmonic frequency. As such, if the second harmonic is expected to cause arcing, six bridges may be used in the chamber to mitigate arcing.

[0018] FIG. 3 shows a cross sectional perspective view of a second embodiment of the chamber 300. This chamber 300 is similar to the chamber 100 of FIGS. 1 and 2, except that the chamber 300 has a metallic wire mesh 310 disposed between the bucket 150 and the chamber sidewall 118. In one embodiment, the mesh 310 comprises a plurality of radially extending wire bridges 302 with a plurality of concentric wire rings 301 connecting the bridges 302. Bridges formed of a metallic mesh function in the same manner as described above. Bridges formed of a metallic mesh provide ground paths from the bucket 150 to the grounded chamber sidewall 118 to eliminate the formation of a standing wave. Additionally, since the mesh 310 is not solid, gases flow

through spaces in the mesh 310.

Claims

1. A plasma assisted semiconductor substrate processing chamber, comprising:
 - an enclosure comprising conductive walls;
 - a substrate support disposed within the enclosure; and
 - a plurality of electrically conductive members connecting a portion of the substrate support with a portion of the walls.
2. The processing chamber of claim 1, wherein the walls comprise a sidewall having an inner surface, and wherein the substrate support comprises a sidewall having an outer surface, and wherein the electrically conductive members connect a portion of the inner surface of the sidewall of the walls with a portion of the outer surface of the sidewall of the substrate support.
3. The processing chamber of claim 1, wherein an RF power source and a DC power source are coupled to a substrate electrode in the substrate support, and wherein the walls are grounded.
4. The processing chamber of claim 3, wherein an insulating material is disposed between the sidewall of the substrate support and the substrate electrode.
5. The processing chamber of claim 1, wherein:
 - the enclosure comprises a grounded sidewall having an inner surface;
 - the substrate support comprises a substrate support member disposed within the enclosure having a sidewall having an outer surface;
 - an RF power source and a DC power source are coupled to the substrate support member; and
 - a plurality of electrically conductive members are connecting a portion of the inner surface of the sidewall of the enclosure with a portion of the outer surface of the sidewall of the substrate support member, wherein the electrically conductive members provide RF ground paths from the sidewall of the substrate support member to the sidewall of the enclosure, and wherein the electrically conductive members are disposed such that electrical arcing is prevented within the enclosure.
6. The processing chamber of claim 1 or 5, wherein the electrically conductive members are equally

spaced from each other.

7. The processing chamber of claim 1 or 5, wherein the electrically conductive members are disposed such that 5
- electrical arcing is prevented within the enclosure: or
the formation of one or more standing waves within the chamber is prevented: or 10
the formation of one or more RF nodes within the chamber is prevented.
8. The processing chamber of claim 1 or 5, wherein the electrically conductive members are disposed such that a largest electrical RF return path length within the enclosure does not exceed approximately 1/4 of a smallest surface RF wavelength formed in the enclosure. 15
- 20
9. The processing chamber of claim 1 or 5, wherein the electrically conductive members are disposed such that a largest electrical RF return path length within the enclosure does not exceed approximately 1/20 of a smallest free space RF wavelength corresponding to a driving frequency and harmonics of the driving frequency formed in the enclosure. 25
10. The plasma assisted semiconductor substrate processing chamber of claim 1, wherein the electrically conductive members are made of metal, in particular of metal mesh. 30
11. The processing chamber of claim 1 or 5, wherein the plasma assisted semiconductor substrate processing chamber is a chemical vapor deposition chamber or an etch chamber. 35
12. The processing chamber of any of the preceding claims, wherein the substrate support member comprises an electrostatic chuck. 40

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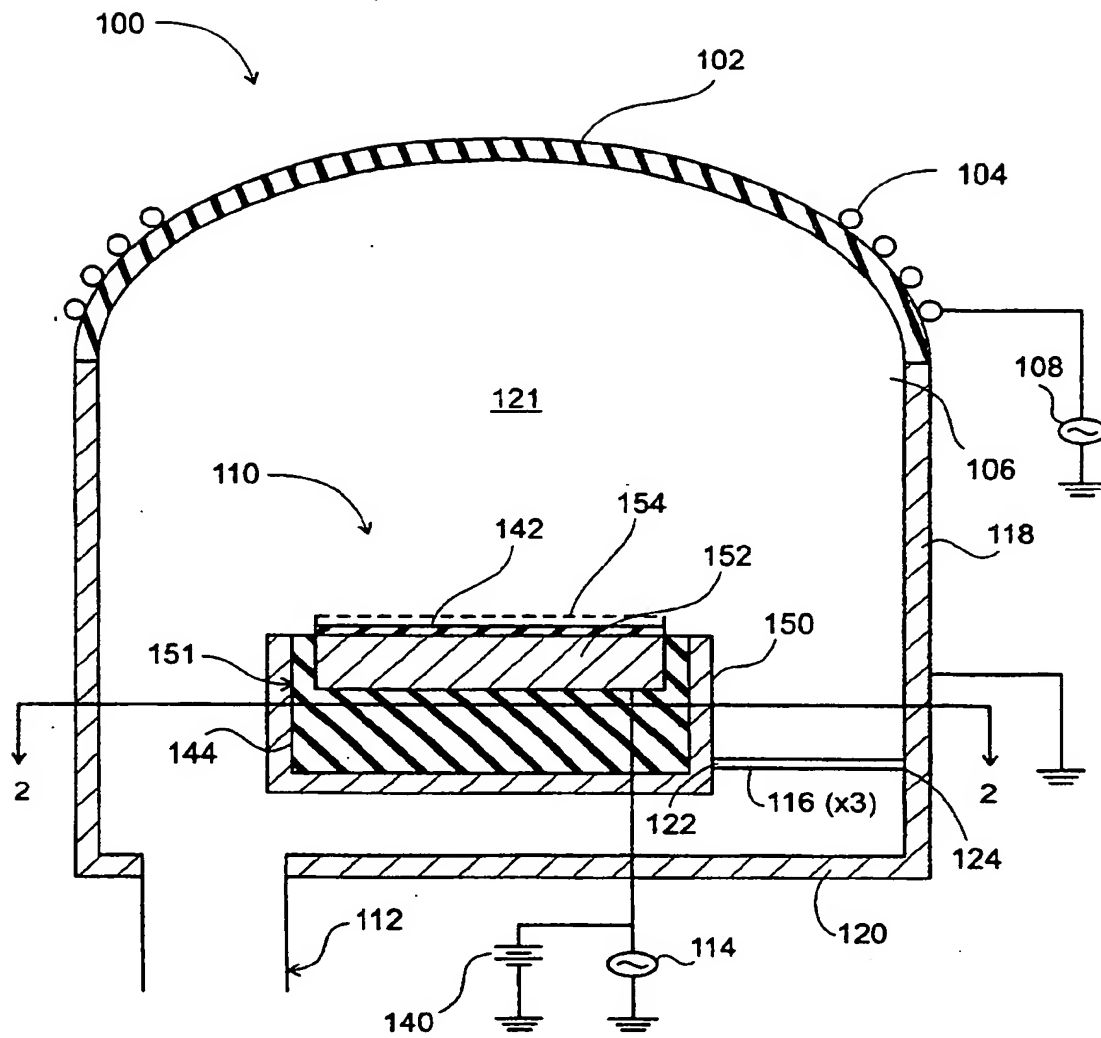


Fig. 1

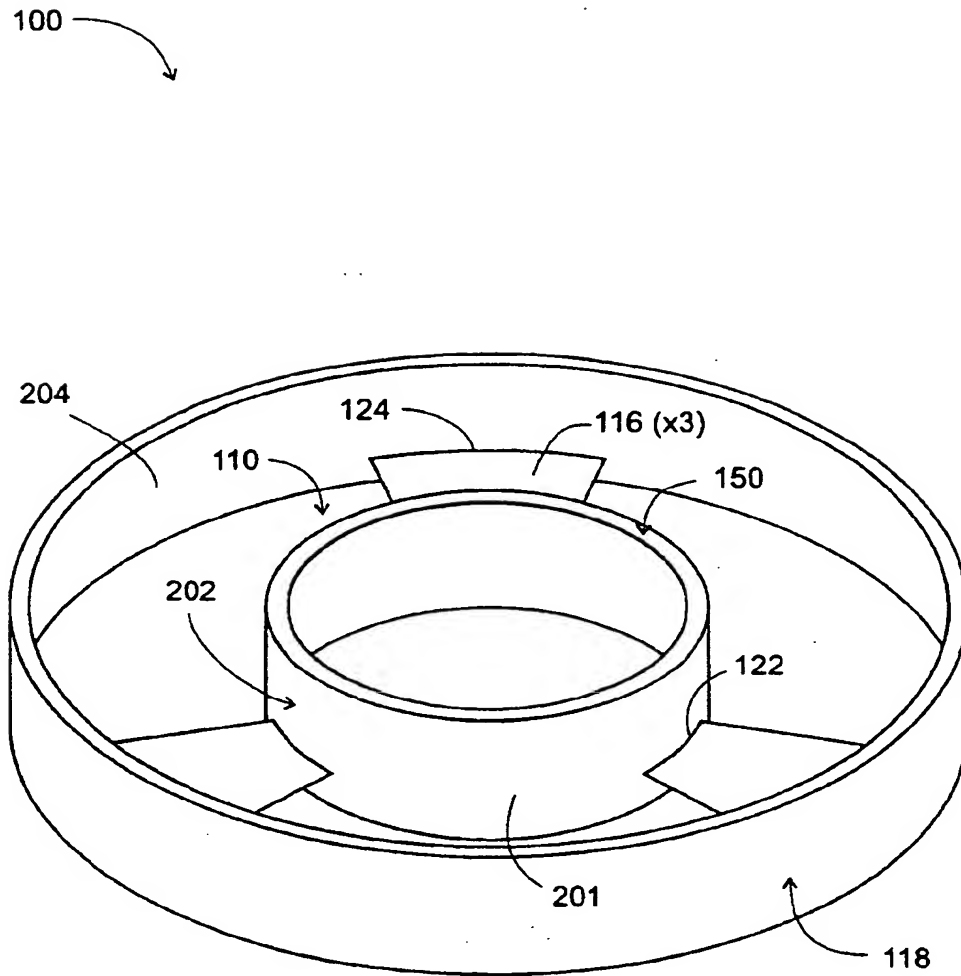


Fig. 2

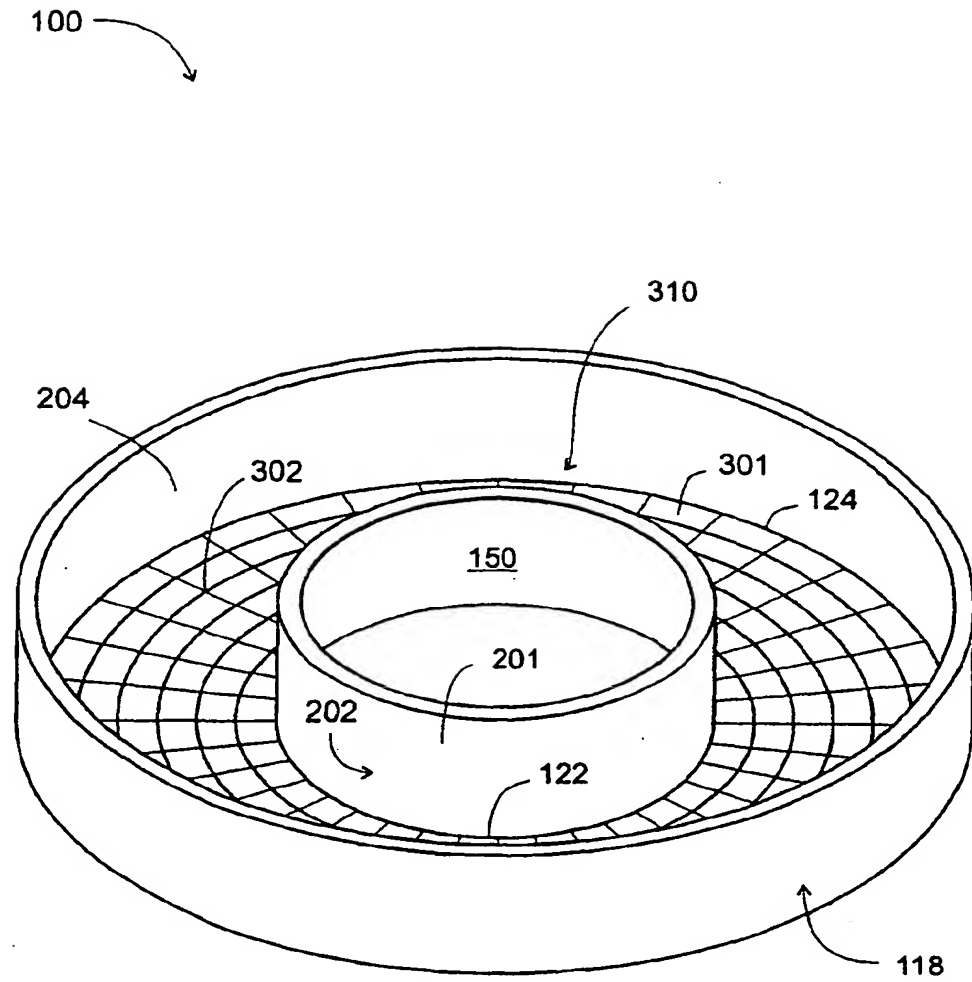


Fig. 3



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Application Number
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Place of search BERLIN		Date of completion of the search 8 April 2004	Examiner Hoffmann, N
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